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				Application Number	Not Yet Assigned		
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S	STATEMENT	BY /	APPLICANT	First Named Inventor	Leonard Forbes		
				Group Art Unit	2826		
<u> </u>	(use as many si	heels as	; necessary)	Examiner Name	Not Yet Assigned		
Sheet	1	of	2	Attorney Docket Number	M4065.0381/P381-A		
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Examiner	Cite No.1	U.S. Patent C	Document	Name of Patentee or Applicant of Cited Document	Date of Publication of	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Initiats*		Number	Kind Code ² (# known)		Cited Document MM-DD-YYYY	
IMI		5,356,821		Naruse et al.	10/1994	
		5,886,368		Forbes et al.	03/1999	
		6,097,070		Mandelman et al.	08/2000	
		6,274,510		Wilk et al.	08/2001	
		6,348,387		Yu	02/2002	
		5,895,487		Boyd et al.	04/1999	
		6,563,151		Shin et al.	05/2003	
		6,114,736		Balasubramanyam et al.	09/2000	
JMJ		6,281,559		Yu et al.	08/2001	
					<u> </u>	

	FOREIGN PATENT DOCUMENTS							
		Foreign Patent Document					Pages, Columns, Lines,	Т
Examiner Initials*	Cite No.1	Office ³	Number ⁴	Kind Cod (if known)	Name of Patentee or Applicant of Cited Document	Oate of Publication of Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear	T⁵
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Examiner Signature	T. M. Thomas	Date Considered	06/08/05

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l				Group Art Unit	N/A		
	(use as many s	heets as	necessary)	Examiner Name	Not Yet Assigned		
Sheet	2	of	2	Attorney Docket Number	M4065.0381/P381		

		OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
1m1	Α	S. Tiwari, et al., "Straddle Gate Transistors: High I _{on} /I _{off} Transistors at Short Gate Lengths" IBM Research Division.	
Jm1	В	W. Long, et al., "Dual-Material Gate (DMG) Field Effect Transistor."	
1m1	С	N. R. Rueger, et al. "Selective Etching of SiO ₂ Over Polycrystalline Silicon Using CHF ₃ in an Inductively Coupled Plasma Reactor."	
1m1	D	S. Vallon, et al., "Polysilicon-germanium Gate Patterning Studies in a High Density Plasma Helicon Source", J. Vac. Sci. Technol. A 15(4), Jul/Aug 1997.	
1m1	E	P. Patel, et al., "Low Temperature VUV Enhanced Growth of Thin Silicon Dioxide Films" Applied Surface Science 46 (1990) 352-356.	
1m1	F	W. Shindo, et al., "Low-Temperature Large-Grain Poly-Si Direct Deposition by Microwave Plasma Enhanced Chemical Vapor Deposition Using SiH ₄ /Xe", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
IMI	G	R. Nozawa, et al., "Low Temperature Polycrystalline Silicon Film Formation With and Without Charged Species in an Electron Cyclotron Resonance SiH ₄ /H ₂ Plasma-Enhanced Chemical Vapor Deposition", J. Vac. Sci. Technol. A 17(5), Sep/Oct 1999.	
1m1	Н	C. Saha, et al., "Ion Assisted Growth and Characterization of Polycrystalline Silicon and Silicon-Germanium Films" (visited Nov. 18, 1999) http://www.dialogselect.com/tech/cgi/pres .	
	l	D. Landheer, et al., "Formation of High-Quality Silicon Dioxide Films by Electron- Cyclotron Resonance Plasma Oxidation and Plasma-Enhanced Chemical Vapour- Deposition" (visited Oct. 21, 1999) http://www.dialogselect.com/tech/cqi/pres	
	J	K. Usami, et al., "Thin Si Oxide Films for MIS Tunnel Emitter by Hollow Cathode- Enhanced Plasma Oxidation" (visited Oct. 21, 1999) ">http://www.di	
	K	K.C. Saraswat, et al. "A Low Temperature Polycrystalline SiGe CMOS TFT Technology for Large Area AMLCD Drivers" (visited 11/18/99) ">http://www.dialogselect.com/tech/cgi/pres>">	

Signature 1 1. M. /hom a.5 Considered 06/08/05	Examiner T. M. Thomas	Date Considered	1 04/00/05 1
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